

氮掺杂石墨烯的 p 型场效应及其精细调控

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Nitrogen Doped Graphene with p -Type Field-Effect and Its Fine Modulation

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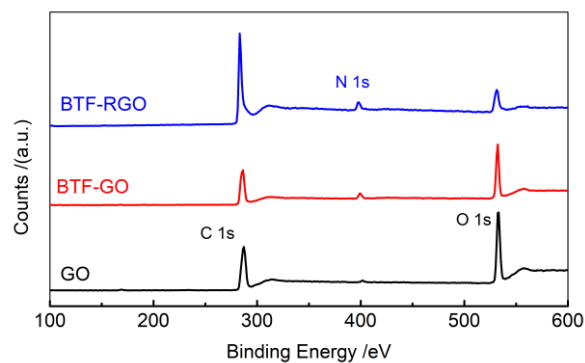


Fig. S1 XPS survey spectra of GO, BTF-GO and BTF-RGO.

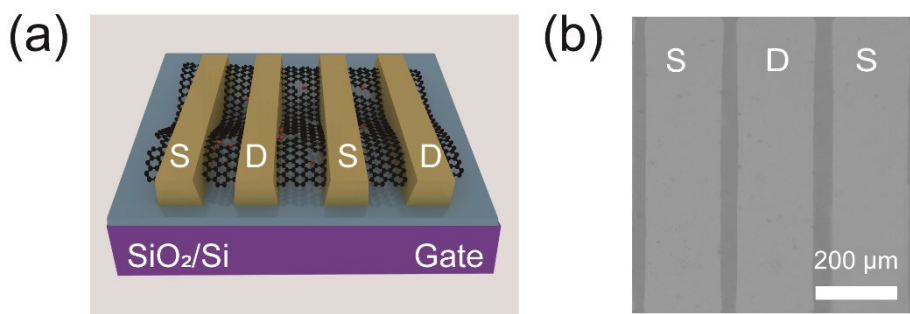


Fig. S2 (a) Schematic and (b) SEM image of a typical FET device.

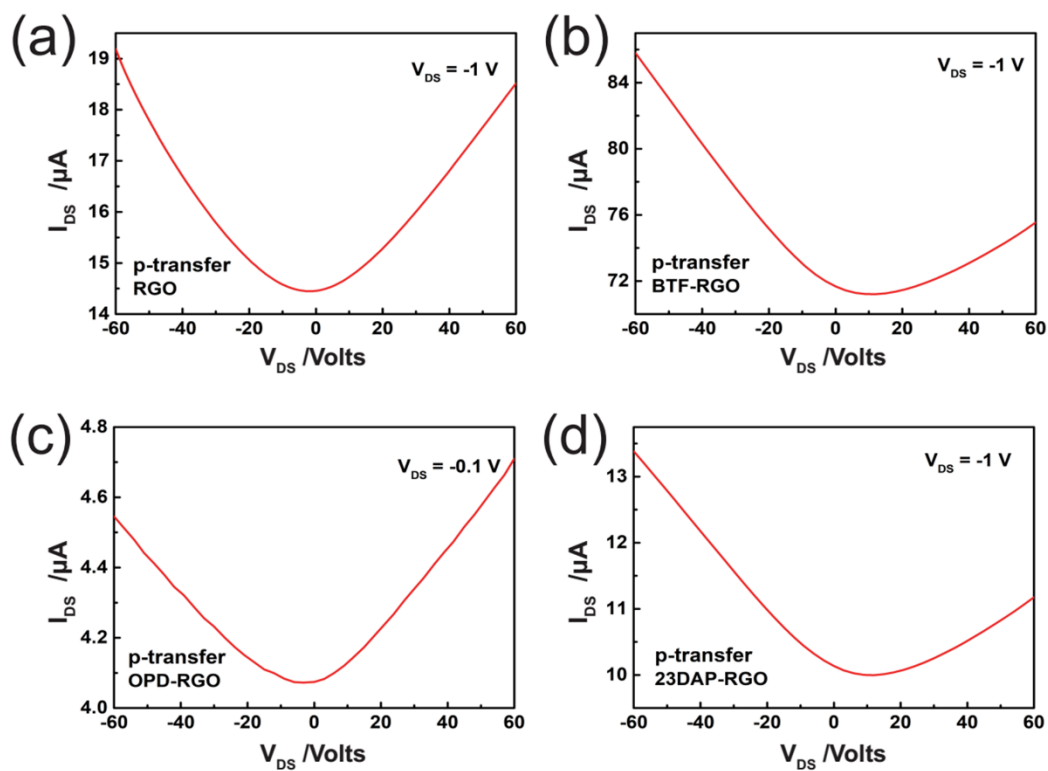


Fig. S3 p-Channel transfer curves of the field-effect transistors based on (a) RGO, (b) BTF-RGO, (c) OPD-RGO and (d) 23 DAP-RGO.

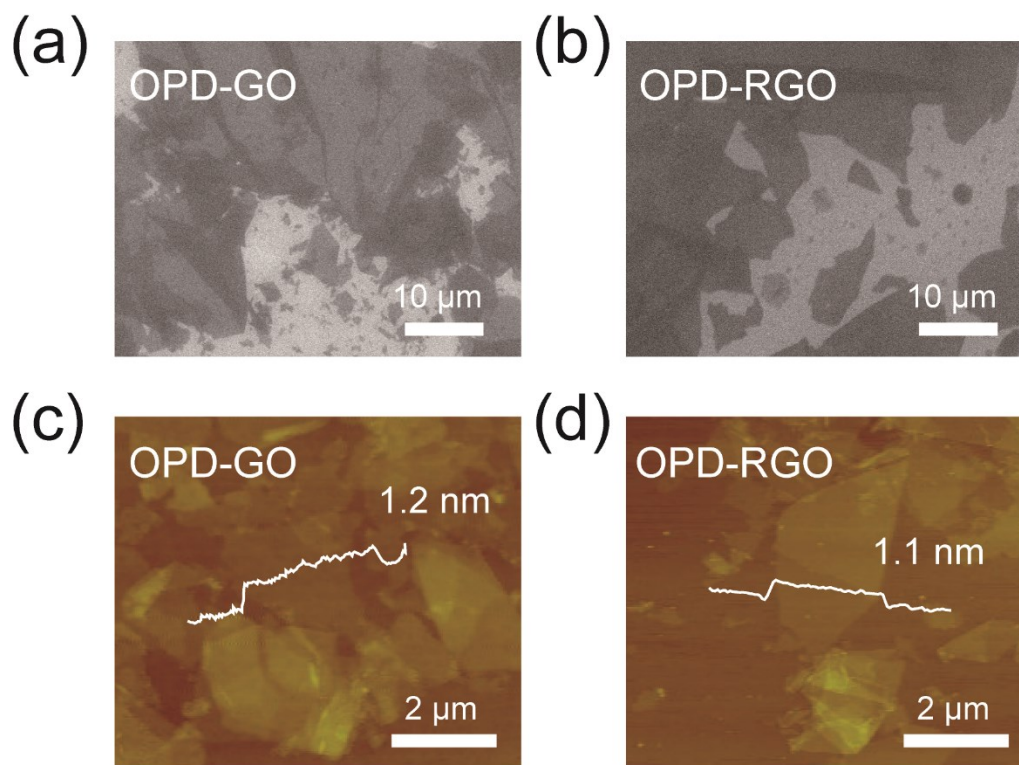


Fig. S4 SEM images of (a) OPD-GO and (b) OPD-RGO. AFM images of (c) OPD-GO and (d) OPD-RGO.

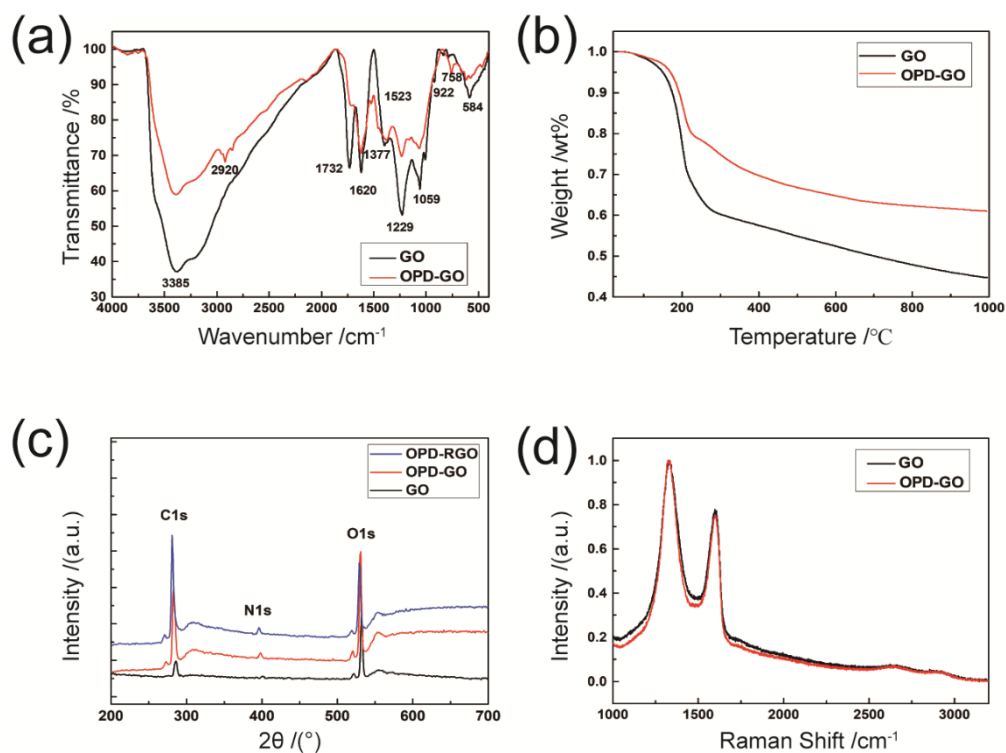


Fig. S5 (a) FT-IR spectra and (b) TGA curves of GO and OPD-GO. (c) XPS survey spectra of GO, OPD-GO and OPD-RGO. (d) Raman spectra of GO and OPD-GO.

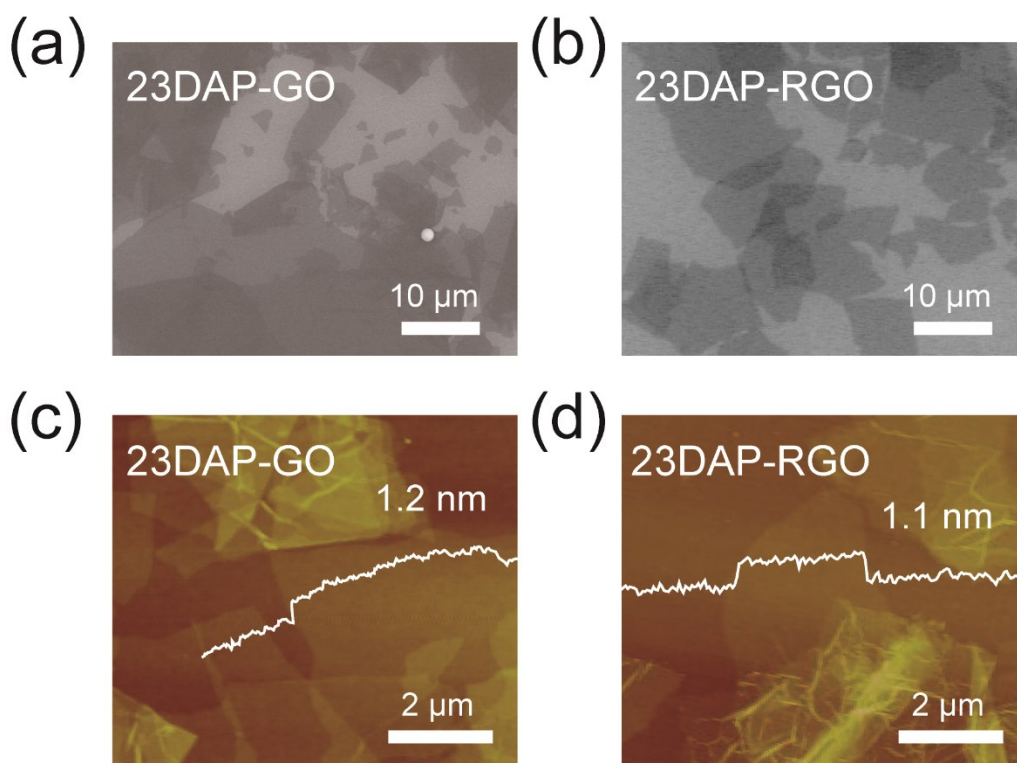


Fig. S6 SEM images of (a) 23DAP-GO and (b) 23DAP-RGO. AFM images of (c) 23DAP-GO and (d) 23DAP-RGO.

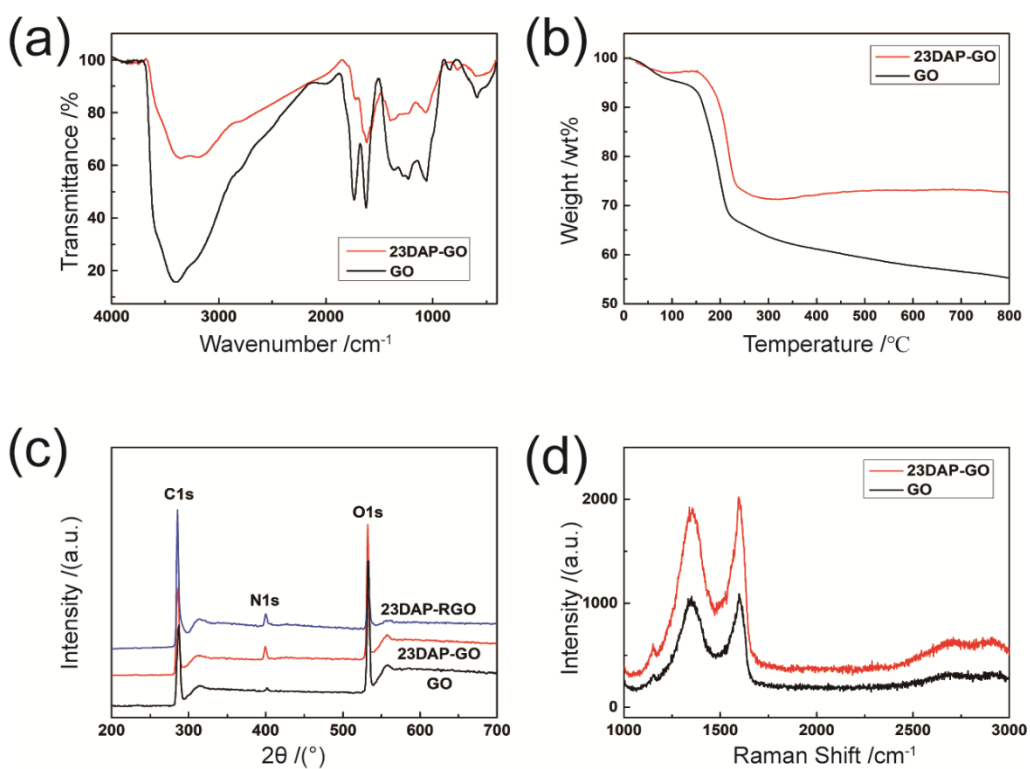


Fig. S7 (a) FT-IR spectra and (b) TGA curves of GO and 23DAP-GO. (c) XPS survey spectra of GO, 23DAP-GO and 23DAP-RGO. (d) Raman spectra of GO and 23DAP-GO.